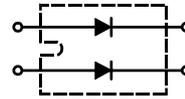


Power Schottky Rectifier

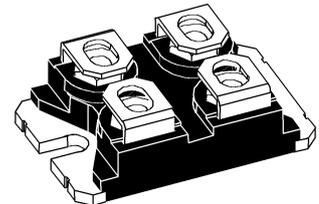
$I_{FAV} = 2 \times 100 \text{ A}$
 $V_{RRM} = 150 \text{ V}$
 $V_F = 0.78 \text{ V}$

Preliminary Data

| V_{RSM} V | V_{RRM} V | Type |
|----------------|----------------|----------------|
| 150 | 150 | DSS 2x101-015A |



miniBLOC, SOT-227 B



| Symbol | Conditions | Maximum Ratings | |
|----------------|--|------------------------------|------------------------|
| I_{FRMS} | | 150 | A |
| I_{FAVM} | $T_C = 110^\circ\text{C}$; rectangular, $d = 0.5$ | 100 | A |
| I_{FAVM} | $T_C = 110^\circ\text{C}$; rectangular, $d = 0.5$; per device | 200 | A |
| I_{FSM} | $T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine | 1200 | A |
| E_{AS} | $I_{AS} = \text{tbd A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive | tbd | mJ |
| I_{AR} | $V_A = 1.5 \cdot V_{RRM}$ typ.; $f = 10 \text{ kHz}$; repetitive | tbd | A |
| $(dv/dt)_{cr}$ | | 18000 | V/ μs |
| T_{VJ} | | -40...+150 | $^\circ\text{C}$ |
| T_{VJM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -40...+150 | $^\circ\text{C}$ |
| P_{tot} | $T_C = 25^\circ\text{C}$ | 310 | W |
| V_{ISOL} | 50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$ | 2500 | V~ |
| M_d | mounting torque (M4) terminal connection torque (M4) | 1.1-1.5/9-13 1.1-1.5/9-13 | Nm/lb.in. Nm/lb.in. |
| Weight | typical | 30 | g |

Features

- International standard package miniBLOC
- Isolation voltage 2500 V~
- UL registered E 72873
- 2 independent Schottky diodes in 1 package
- Very low V_F
- Extremely low switching losses
- Low I_{RM} -values

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see outlines.pdf

| Symbol | Conditions | Characteristic Values | |
|--------------------------|---|-----------------------|------------|
| | | typ. | max. |
| I_R ① | $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$ | 4 | mA |
| | | 40 | mA |
| V_F | $I_F = 100 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 100 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 200 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ | 0.78 | V |
| | | 0.90 | V |
| | | 0.99 | V |
| R_{thJC} R_{thCH} | 0.1 | 0.4 | K/W K/W |

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

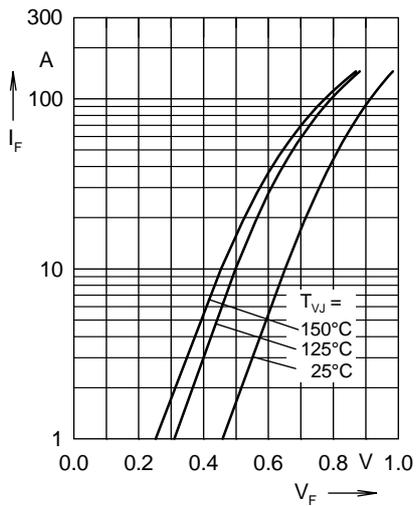


Fig. 1 Maximum forward voltage drop characteristics

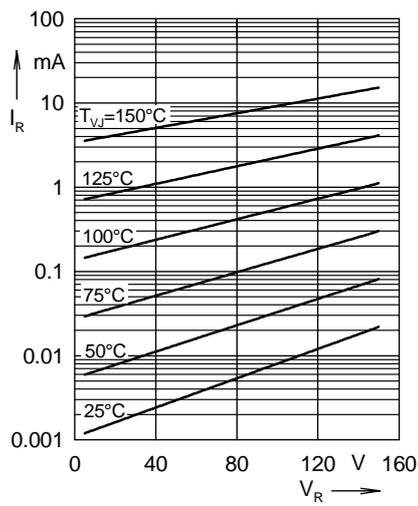


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

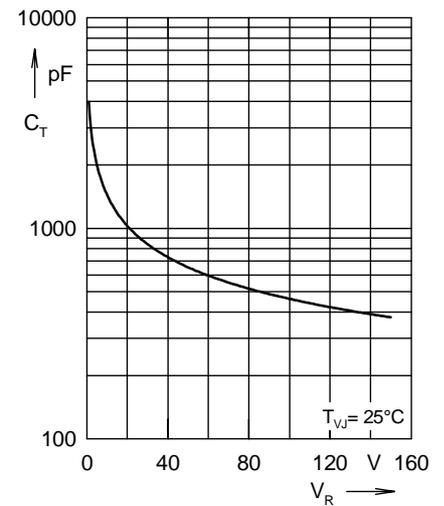


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

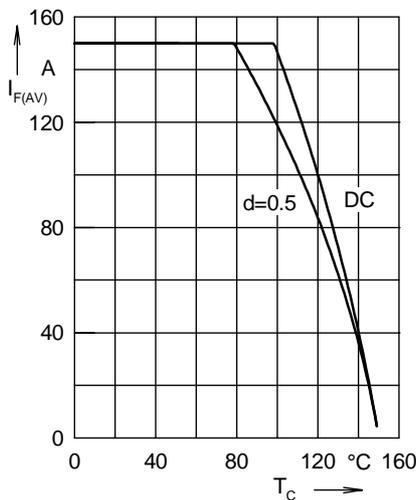


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

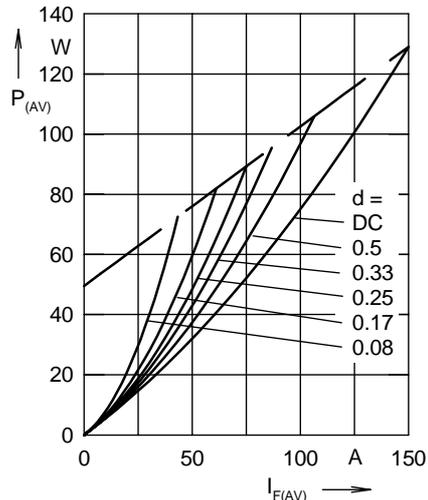


Fig. 5 Forward power loss characteristics

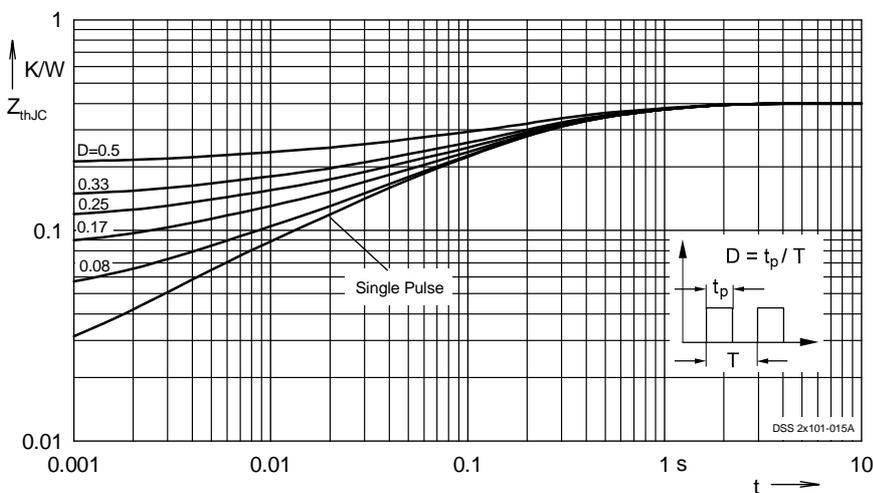


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode